Amendments to the Claims:

Without prejudice, this listing of the claims replaces all prior versions and listings of the claims in the present application:

Listing of Claims:

1.-23. (Canceled)

24. (Currently Amended) An arrangement, comprising:

p-doped semiconductor layers;

n-doped semiconductor layers; and

a plurality of transitions arranged between the p-doped semiconductor layers and the n-doped semiconductor layers, the transitions displaying a Zener breakdown upon application of a characteristic voltage for each of the transitions, wherein:

the characteristic voltages of the transitions additively correspond to a breakdown voltage of the arrangement,

the p-doped semiconductor layers and the n-doped semiconductor layers are highly doped,

the p-doped semiconductor layers form at least two groups doped at different concentrations, a highly doped layer of the p-doped semiconductor layers being doped at about 2×10^{18} atoms/cm^3,

the n-doped semiconductor layers form at least two groups that are doped at different concentrations, a highly doped layer of the n-doped semiconductor layers being doped at about 2×10^{18} atoms/cm^3,

the p-doped semiconductor layers and the n-doped semiconductor layers exhibit a constant doping, and

the p-doped semiconductor layers and the n-doped semiconductor layers are doped at a same concentration, wherein the p-doped semiconductor layers and the n-doped semiconductor layers have a thickness of approximately 4μm.

25. – 29. (Canceled)

30. (Previously Presented) The arrangement according to claim 24, further comprising:

an n-doped substrate on which are arranged the p-doped semiconductor layers and the n-doped semiconductor layers.

31. (Previously Presented) The arrangement according to claim 30, wherein a doping type of a semiconductor layer farthest away from the n-doped substrate corresponds to a doping type of the n-doped substrate.

32. (Previously Presented) The arrangement according to claim 30, wherein a doping type of a semiconductor layer farthest away from the n-doped substrate is different than a doping type of the n-doped substrate.

33. (Previously Presented) The arrangement according to claim 30, wherein the n-doped substrate has a thickness of approximately 500μm.

34. (Previously Presented) The arrangement according to claim 24, further comprising:

a p-doped substrate on which are arranged the p-doped semiconductor layers and the n-doped semiconductor layers.

35. (Previously Presented) The arrangement according to claim 34, wherein a doping type of a semiconductor layer farthest away from the p-doped substrate corresponds to a doping type of the p-doped substrate.

36. (Previously Presented) The arrangement according to claim 34, wherein a doping type of a semiconductor layer farthest away from the p-doped substrate is different than a doping type of the p-doped substrate.

37. (Previously Presented) The arrangement according to claim 35, wherein the p-doped substrate has a thickness of approximately 500μm.

38. (Canceled)

39. (Previously Presented) The arrangement according to claim 24, wherein a concentration of doping for the p-doped semiconductor layers and the n-doped semiconductor layers is approximately 2×10^{19} atoms/cm^3.

40. (Previously Presented) The arrangement according to claim 24, wherein ten transitions are provided between the p-doped semiconductor layers and the n-doped semiconductor layers.

41. (Previously Presented) The arrangement according to claim 24, further comprising:

metal contacts arranged over an entire respective surface of an upper side and a lower side of the arrangement.

42. (Previously Presented) The arrangement according to claim 24, wherein the n-doped semiconductor layers and the p-doped semiconductor layers are silicon layers.

43.-47. (Canceled)